

# 2SD1577

## Silicon NPN Triple-Diffused Junction Mesa Type

### Horizontal Deflection Output

#### ■ Features

- High breakdown voltage and high reliability by glass passivation
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

#### ■ Absolute Maximum Ratings (Tc=25°C)

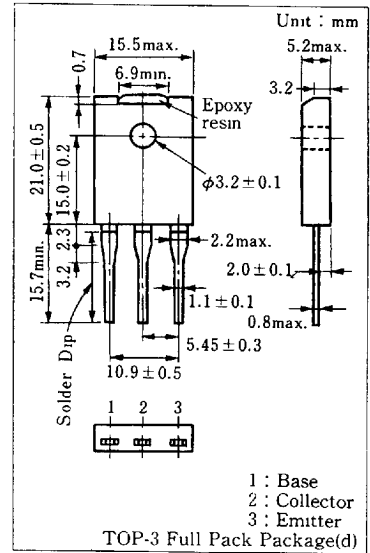
Item	Symbol	Value	Unit
Collector-base voltage	V <sub>CB0</sub>	1500	V
Collector-emitter voltage	V <sub>CEs</sub>	1500	V
	V <sub>CE0</sub>	700	V
Emitter-base voltage	V <sub>EB0</sub>	6	V
Collector current	I <sub>C</sub>	5	A
Peak collector current	I <sub>CP</sub> *	17	A
Peak base current	I <sub>BP</sub>	3.5	A
Reverse peak base current	I <sub>BP</sub>	-2.5	A
Collector power dissipation	T <sub>c</sub> =25°C	100	W
	T <sub>a</sub> =25°C	3	
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

\* Non-repetitive peak value

#### ■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min	typ.	max.	Unit
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> =750 V, I <sub>E</sub> =0			50	μA
		V <sub>CB</sub> =1500 V, I <sub>E</sub> =0			1	mA
Emitter-base voltage	V <sub>EBO</sub>	I <sub>E</sub> =1 mA, I <sub>C</sub> =0	6			V
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =4A	4		15	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =4.5A, I <sub>B</sub> =2 A			2	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =4.5 A, I <sub>B</sub> =2 A			1.3	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =0.5A, f=0.5MHz		2		MHz
Fall time	t <sub>f</sub>	I <sub>C</sub> =4 A, I <sub>Bend</sub> =1.5 A			1	μs
Storage time	t <sub>stg</sub>	L <sub>B</sub> =10 μH			11	μs

#### ■ Package Dimensions



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